Product data sheet

1. General description

EEPP[™]- Efficiency Enhanced Pt Planar rectifier in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- Planar termination structure
- High operating temperature capability (T_{i (max)} = 175°C)
- Higher I_{FSM} capability

3. Applications

- · Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		1200				V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_{mb} \le 123$ °C; Fig. 1; Fig. 2; Fig. 3	8			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 123 °C; square-wave pulse	16		А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;			Α		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.4	3.2	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	2.0	-	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	55	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; connected to cathod	1 2 TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package	² ackage					
	Name	Description	Version				
BYC8-1200P		Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59				

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC8-1200P	BYC8-1200P

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V_R	reverse voltage	DC	1200	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; $T_{mb} \le 123$ °C; Fig. 1; Fig. 2; Fig. 3	8	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 123 °C$; square-wave pulse	16	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	110	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

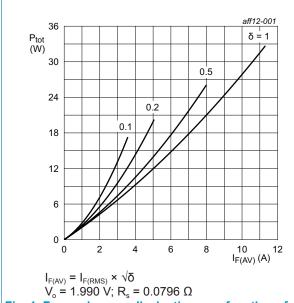
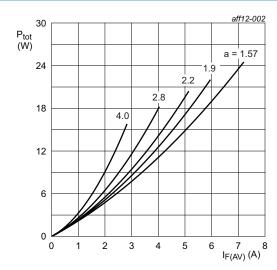


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

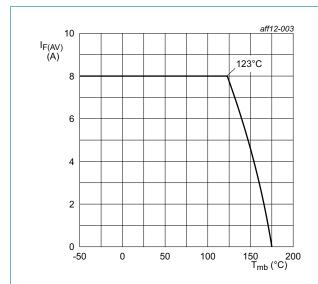


a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 1.990 V; Rs = 0.0796 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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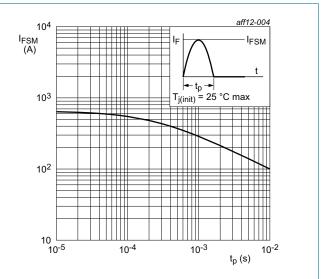


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

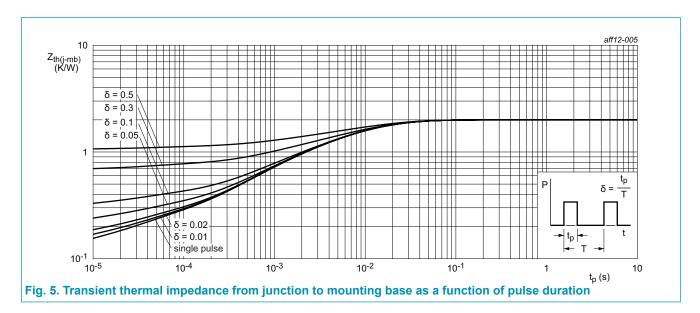
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



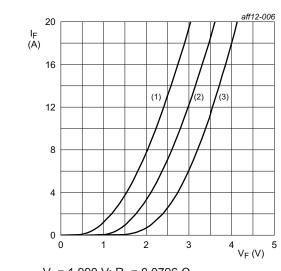
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F	forward current	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.4	3.2	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	2.0	-	V
I _R	reverse current	V _R = 1200 V; T _j = 25 °C	-	-	100	μA
		V _R = 1200 V; T _j = 150 °C	-	-	0.5	mA
Dynamic	characteristics			•		
Q_r	reverse charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	215	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	475	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	525	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	-	55	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	46	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	85	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/µs};$ $T_j = 150 \text{ °C}; Fig. 7$	-	90	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/µs};$ $T_j = 25 \text{ °C}; Fig. 7$	-	9.2	-	А
		I _F = 8 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	11.2	-	А
		I _F = 8 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _i = 150 °C; Fig. 7	-	12	-	А



 V_o = 1.990 V; R_s = 0.0796 Ω

(1) $T_j = 150$ °C; typical values (2) $T_j = 150$ °C; maximum values

(3) T_i = 25 °C; maximum values



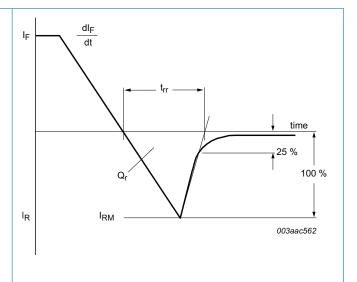
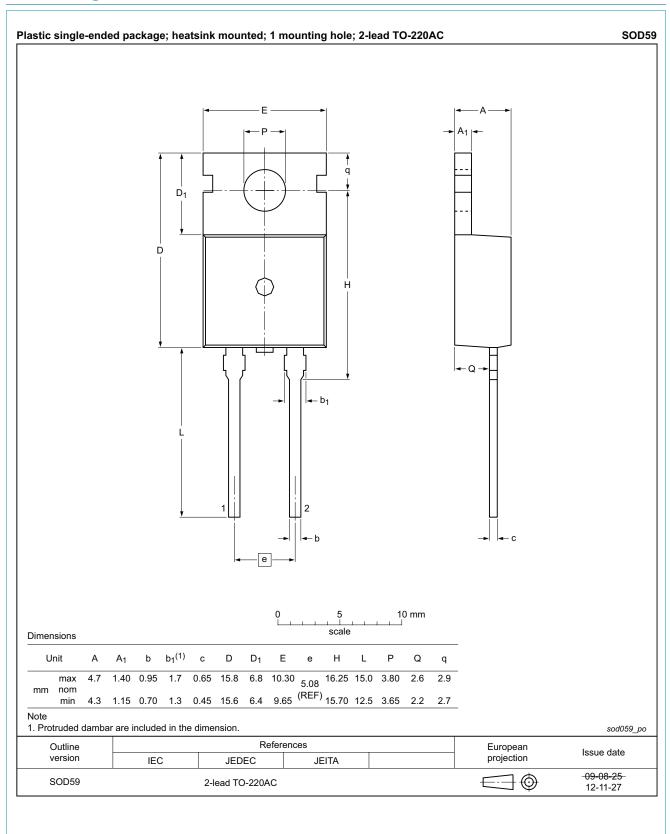


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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